

IN THE CLAIMS

1. (Previously Presented) A method of fabricating a semiconductor device having a recess region in an insulation layer on a silicon substrate, the method comprising the steps of:

depositing a barrier metal ¹⁰⁹ on the whole surface of the insulation layer including the substrate surface in the recess region;

depositing selectively an anti-nucleation layer ¹¹³ on the barrier metal except in the recess region;

depositing a CVD-Al layer ¹¹⁷ on the barrier metal in the recess region;

depositing a metal or a metal alloy for inhibiting aluminum migration on the anti-nucleation layer and the barrier metal except in the recess region; and

depositing a PVD-Al layer ^{119 col 4} and reflowing the PVD-Al layer.

FIG. 4

FIG. 5

2. (Original) The fabrication method of claim 1, wherein the metal or the metal alloy inhibiting aluminum migration is one of Ti, TiN, Ti/TiN, Ta, TaN and Ta/TaN.

3. (Original) The fabrication method of claim 1, wherein a deposition thickness of the metal or the metal alloy inhibiting aluminum migration is less than 100 Å.